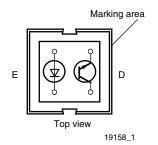


Vishay Semiconductors

Reflective Optical Sensor with Transistor Output



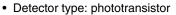


DESCRIPTION

The CNY70 is a reflective sensor that includes an infrared emitter and phototransistor in a leaded package which blocks visible light.

FEATURES

· Package type: leaded



• Dimensions (L x W x H in mm): 7 x 7 x 6

• Peak operating distance: < 0.5 mm

• Operating range within > 20 % relative collector current: 0 mm to 5 mm

Typical output current under test: I_C = 1 mA

• Emitter wavelength: 950 nm

· Daylight blocking filter

· Lead (Pb)-free soldering released

• Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC





APPLICATIONS

· Optoelectronic scanning and switching devices i.e., index sensing, coded disk scanning etc. (optoelectronic encoder assemblies).

PRODUCT SUMMARY					
PART NUMBER	DISTANCE FOR MAXIMUM CTR _{rel} (1) (mm)	DISTANCE RANGE FOR RELATIVE I _{out} > 20 % (mm)	TYPICAL OUTPUT CURRENT UNDER TEST (2) (mA)	DAYLIGHT BLOCKING FILTER INTEGRATED	
CNY70	0	0 to 5	1	Yes	

Notes

 $^{(1)}$ CTR: current transfere ratio, I_{out}/I_{in}

(2) Conditions like in table basic charactristics/sensors

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	VOLUME (1)	REMARKS		
CNY70	Tube	MOQ: 4000 pcs, 80 pcs/tube	-		

Note

(1) MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (1)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
COUPLER					
Total power dissipation	T _{amb} ≤ 25 °C	P _{tot}	200	mW	
Ambient temperature range		T _{amb}	- 40 to + 85	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	Distance to case 2 mm, t ≤ 5 s	T _{sd}	260	°C	
INPUT (EMITTER)					
Reverse voltage		V _R	5	V	
Forward current		I _F	50	mA	
Forward surge current	t _p ≤ 10 μs	I _{FSM}	3	Α	
Power dissipation	T _{amb} ≤ 25 °C	P _V	100	mW	
Junction temperature		T _i	100	°C	

Vishay Semiconductors

Reflective Optical Sensor with **Transistor Output**



ABSOLUTE MAXIMUM RATINGS (1)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
OUTPUT (DETECTOR)					
Collector emitter voltage		V _{CEO}	32	V	
Emitter collector voltage		V _{ECO}	7	V	
Collector current		Ic	50	mA	
Power dissipation	T _{amb} ≤ 25 °C	P _V	100	mW	
Junction temperature		Tj	100	°C	

Note

ABSOLUTE MAXIMUM RATINGS

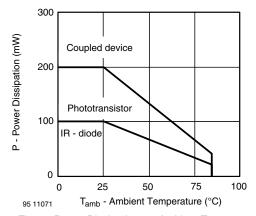


Fig. 1 - Power Dissipation vs. Ambient Temperature

BASIC CHARACTERISTICS (1)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
COUPLER						
Collector current	V _{CE} = 5 V, I _F = 20 mA, d = 0.3 mm (figure 1)	I _C ⁽²⁾	0.3	1.0		mA
Cross talk current	$V_{CE} = 5 \text{ V}, I_F = 20 \text{ mA}, \text{ (figure 2)}$	I _{CX} (3)			600	nA
Collector emitter saturation voltage	$I_F = 20 \text{ mA}, I_C = 0.1 \text{ mA},$ d = 0.3 mm (figure 1)	V _{CEsat} (2)			0.3	V
INPUT (EMITTER)						
Forward voltage	I _F = 50 mA	V _F		1.25	1.6	V
Radiant intensity	$I_F = 50 \text{ mA}, t_p = 20 \text{ ms}$	l _e			7.5	mW/sr
Peak wavelength	I _F = 100 mA	λ _P	940			nm
Virtual source diameter	Method: 63 % encircled energy	d		1.2		mm
OUTPUT (DETECTOR)						
Collector emitter voltage	I _C = 1 mA	V_{CEO}	32			V
Emitter collector voltage	I _E = 100 μA	V _{ECO}	5			V
Collector dark current	$V_{CE} = 20 \text{ V}, I_F = 0 \text{ A}, E = 0 \text{ Ix}$	I _{CEO}			200	nA

Notes

- $^{(1)}$ T_{amb} = 25 °C, unless otherwise specified $^{(2)}$ Measured with the "Kodak neutral test card", white side with 90 % diffuse reflectance
- (3) Measured without reflecting medium

 $^{^{(1)}}$ $T_{amb} = 25$ °C, unless otherwise specified



Reflective Optical Sensor with Transistor Output

Vishay Semiconductors

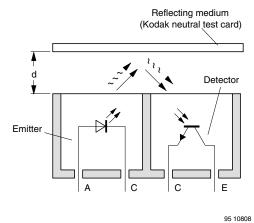


Fig. 2 - Pulse diagram

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

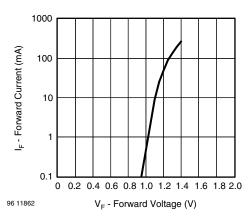


Fig. 3 - Forward Current vs. Forward Voltage

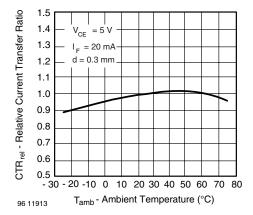


Fig. 4 - Relative Current Transfer Ratio vs. Ambient Temperature

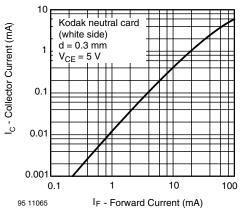


Fig. 5 - Collector Current vs. Forward Current

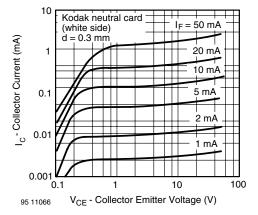


Fig. 6 - Collector Current vs. Collector Emitter Voltage

Vishay Semiconductors

Reflective Optical Sensor with Transistor Output



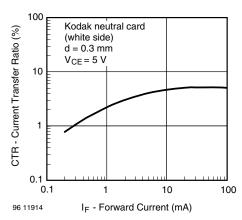
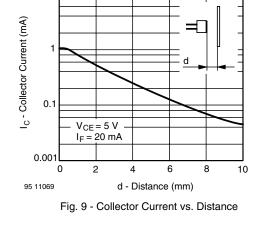


Fig. 7 - Current Transfer Ratio vs. Forward Current



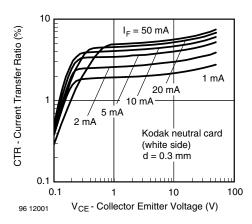


Fig. 8 - Current Transfer Ratio vs. Collector Emitter Voltage

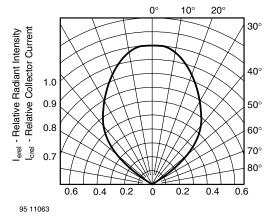


Fig. 10 - Relative Radiant Intensity/Collector Current vs.

Angular Displacement

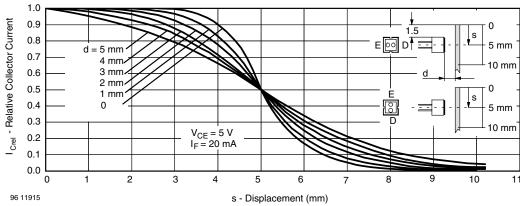


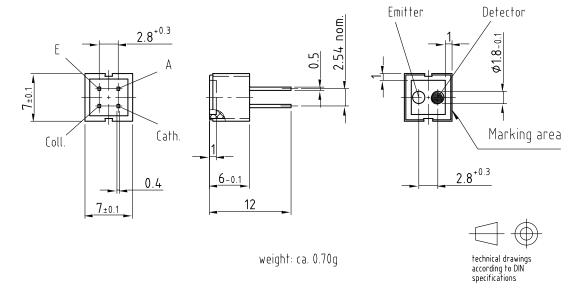
Fig. 11 - Relative Collector Current vs. Displacement



Reflective Optical Sensor with Transistor Output

Vishay Semiconductors

PACKAGE DIMENSIONS in millimeters

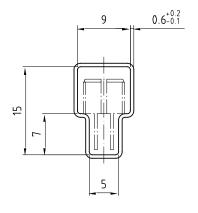


Drawing-No.: 6.544-5062.01-4

Issue: 6; 03.05.06

95 11345

TUBE DIMENSIONS in millimeters



With rubber stopper Tolerance: ±0.5mm Length: 575±1mm

Drawing-No.: 9.700-5097.01-4

Issue: 1; 25.02.00

20291



Vishay

Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.

Document Number: 91000 Revision: 18-Jul-08